

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Canceled)

Claim 2 (Currently Amended): A method of manufacturing a semiconductor device, comprising:

forming a gate electrode on a silicon substrate;

forming a first spacers on respective side surfaces of the gate electrode;

chipping off a surface of the silicon substrate using the gate electrode and the first spacers as masks, to thereby form steplike portions at positions adjacent to base portions of the first spacers;

forming second spacers respectively at the steplike portions; and

forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 1,~~

wherein the steplike portions are respectively formed so as to have upward slanting surfaces.

Claim 3 (Canceled)

Claim 4 (Currently Amended): A method of manufacturing a semiconductor device,
comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the
first spacers as masks, to thereby form steplike portions at positions adjacent to base
portions of the first spacers;
forming second spacers respectively at the steplike portions; and
forming silicides on the silicon substrate using the first spacers and the second
spacers as masks ~~The method according to claim 1,~~

wherein the steplike portions are respectively formed so as to have curved
surfaces convex to the gate electrode.

Claim 5 (Currently Amended): A method of manufacturing a semiconductor device,
comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the
first spacers as masks, to thereby form steplike portions at positions adjacent to base
portions of the first spacers;
forming second spacers respectively at the steplike portions; and

forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 1,~~
wherein the steplike portions are respectively formed so as to have downward slanting surfaces.

Claims 6-10 (Canceled)

Claim 11 (Currently Amended): A method of manufacturing a semiconductor device, comprising:

forming a gate electrode on a silicon substrate;
forming a first spacers on respective side surfaces of the gate electrode;
chipping off a surface of the silicon substrate using the gate electrode and the first spacers as masks, to thereby form steplike portions at positions adjacent to base portions of the first spacers;

forming second spacers respectively at the steplike portions; and
forming silicides on the silicon substrate using the first spacers and the second spacers as masks ~~The method according to claim 10,~~

wherein said forming the formation of the second spacers is done by comprises

forming an oxide film for covering the surface of that covers the silicon substrate, the gate electrode, and the first spacers, thereafter

covering portions other than a device region[[,]] of the silicon substrate

surface with a resist pattern and

anisotropically etching the oxide film ~~in this condition~~ using the resist.